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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/802,735	03/18/2004	Yutaka Takafuji	1035-501	5007

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EXAMINER

TRAN, THIEN F

ART UNIT	PAPER NUMBER
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2811

DATE MAILED: 08/04/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/802,735

Applicant(s)

TAKAFUJI ET AL.

Examiner

Thien F. Tran

Art Unit

2811

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 23 May 2006.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1,3-15,17-32 and 43-55 is/are pending in the application.
- 4a) Of the above claim(s) 6-8,11,17-32 and 43-50 is/are withdrawn from consideration.
- 5) ☐ Claim(s) 54 and 55 is/are allowed.
- 6) ☒ Claim(s) 1,3-5,12-15,51 and 52 is/are rejected.
- 7) ☐ Claim(s) 9,10 and 53 is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____.
- 4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____.

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1, 3, 5, 51 and 52 are rejected under 35 U.S.C. 102(e) as being anticipated by Katayama (US 6,750,476).

Katayama discloses a semiconductor device (Fig. 1) comprising an insulating substrate (10) having a surface on which a first SiO₂ (12) film is formed; a single-crystal silicon thin film (1a) having bonded thereto a second SiO₂ (13) film, which single-crystal silicon thin film is bonded with the insulating substrate on a partial region of the insulating substrate via the first and second SiO₂ films, the single-crystal silicon thin film having a substantially uniform thickness and a substantially damage-free surface; and a non-single-crystal silicon thin film (204) formed on the insulating substrate in a region where the single-crystal silicon thin film is not bonded with the insulating substrate, which non-single-crystal silicon thin film is formed on the insulating substrate via the first SiO₂ film (12) and a third SiO₂ film (41), wherein the second SiO₂ film (13) and the third SiO₂ film (41) are of different thicknesses.

Regarding claim 3, the single-crystal silicon thin film (1a) has a thickness of 30nm.

Regarding claim 5, the non-single crystal silicon thin film (204) comprises polycrystalline silicon.

Regarding claim 52, transistor elements are formed from the single crystal silicon thin film.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claim 4 is rejected under 35 U.S.C. 103(a) as being unpatentable over Katayama (US 6,750,476).

Katayama as described above does not specifically disclose the single crystal silicon thin film (1a) having a thickness of not more than about 20 nm. It would have been obvious to one having ordinary skill in the art at the time the invention was made to form the thickness of the single crystal silicon thin film having the claimed range of thickness to reduce the device size as small as possible, since it has been held that where the general conditions of a claim are disclosed in the prior art, discovering the optimum or workable ranges involves only routine skill in the art. In re Aller, 105 USPQ 233.

Claims 12-15 are rejected under 35 U.S.C. 103(a) as being unpatentable over Katayama (US 6,750,476) in view of Yale (EP 0 559 389).

Katayama as described above does not explicitly disclose the insulating substrate being a high-strain-point glass including an alkaline earth alumino borosilicate glass. Yale discloses a high-strain-point glass as a material for a substrate in liquid crystal display devices. Therefore, it would have been obvious to a person having ordinary skill in the art at the time the invention was made to form the glass substrate of Katayama of the high-strain-point glass disclosed by Yale in order to provide a glass substrate capable of withstanding elevated temperatures and improving the resistance of the glass to chemical attack by reagents.

Regarding claim 13, Yale discloses the insulating substrate being made of barium-alumino borosilicate glass.

Regarding claim 14, Katayama in view of Yale discloses the same structure as claimed wherein the insulating substrate and the single crystal silicon thin film have the same materials as those used in the instant invention. Therefore, it is inherent that the structure of Katayama in view of Yale provides the same characteristics as claimed wherein a difference of linear expansion between the insulating substrate and the single crystal silicon thin film is about not more than 250 ppm at temperatures in a range between substantially room temperature and 600°C.

Regarding claim 15, the insulating substrate as taught by Yale has the same materials as the material used for the insulating substrate in the instant invention. These

materials for the insulating substrate are inherently high-strain-point glasses whose strain point is not less than 500°C.

Allowable Subject Matter

Claims 54 and 55 are allowed.

Claims 9, 10 and 53 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Response to Arguments

Applicant's arguments with respect to claims 1, 3-5, 12-15, 51 and 52 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire **THREE MONTHS** from the mailing date of this action. In the event a first reply is filed within **TWO MONTHS** of the mailing date of this final action and the advisory action is not mailed until after the end of the **THREE-MONTH** shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of

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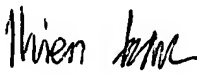
the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thien F. Tran whose telephone number is (571) 272-1665. The examiner can normally be reached on 8:30AM - 5:00PM Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie C. Lee can be reached on (571) 272-1732. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

tt
August 01, 2006


Thien Tran
Primary Examiner